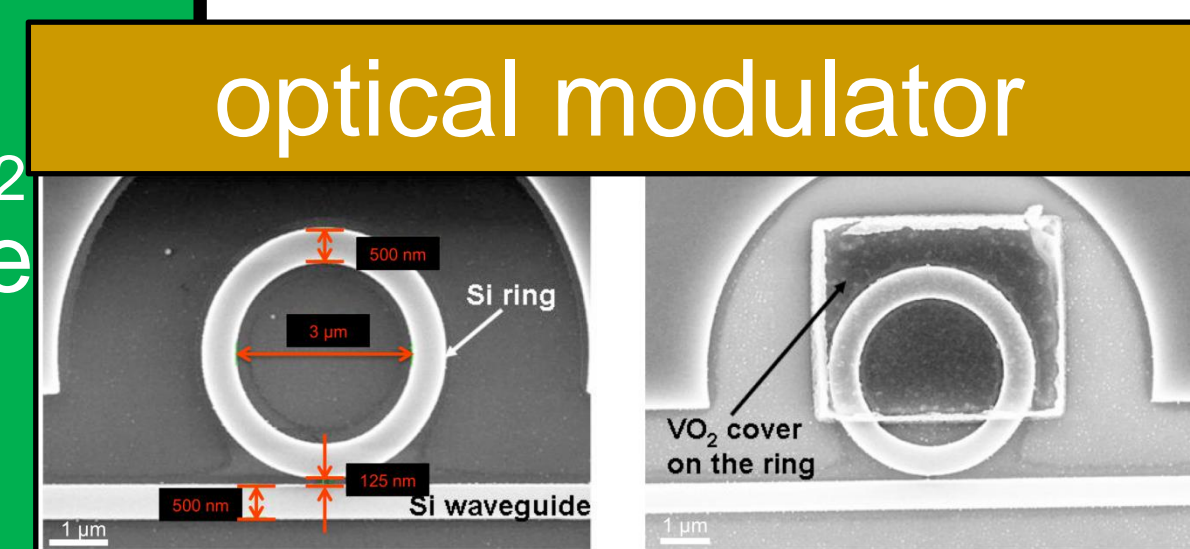


Introduction

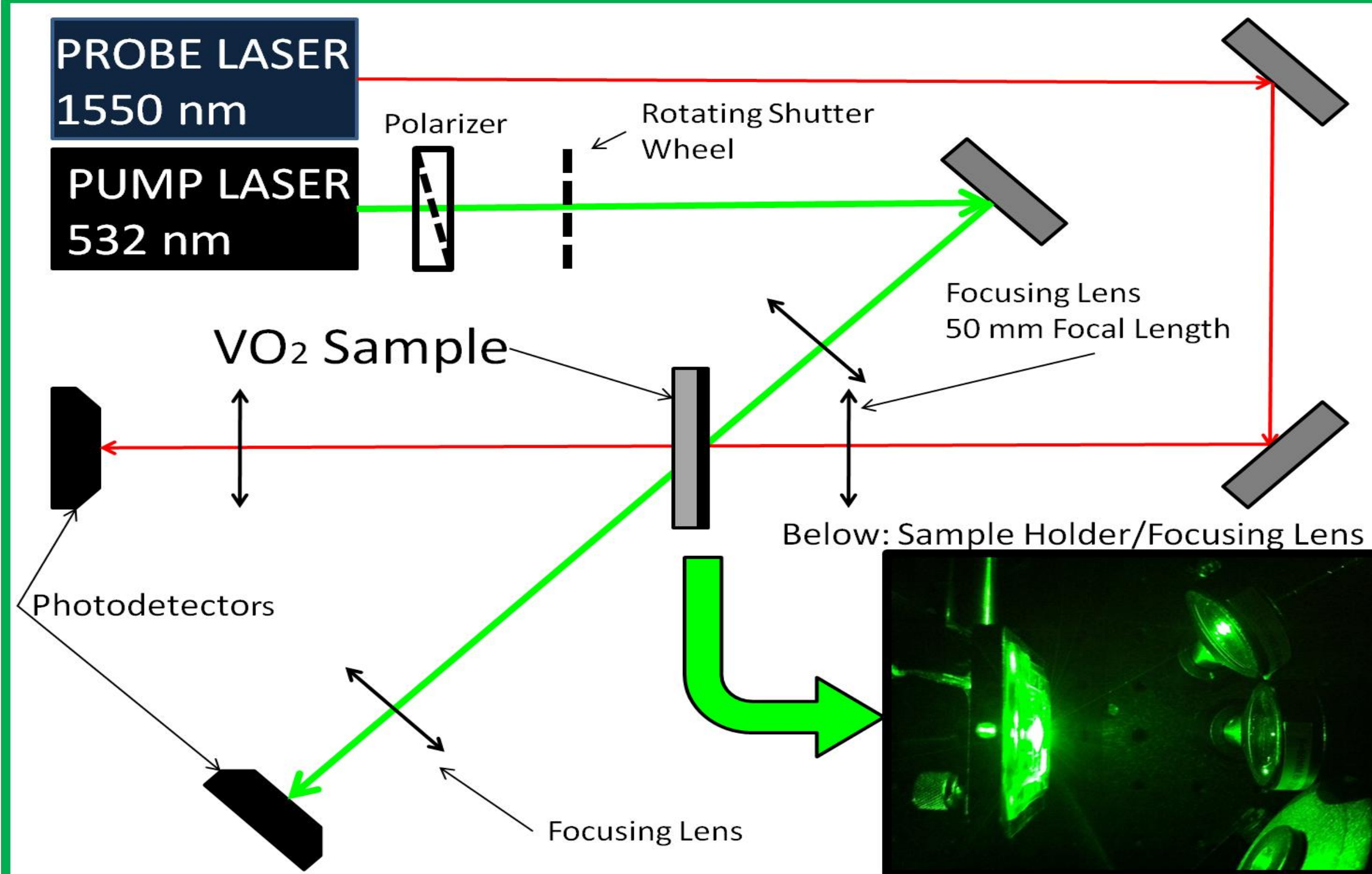
Vanadium dioxide (VO_2) is widely studied for its semiconductor-to-metal phase transition. When heated above 68°C (340 K), VO_2 becomes much more conductive and much less transparent to light. Since VO_2 's phase transition involves a significant change in its refractive index, it has the potential to be used in high speed photonic devices such as optical modulators (1).

Research Goals

- 1) Switch thin films of VO_2 using a low-power laser
- 2) Simulate laser induced temperature rise
- 3) Long term: develop VO_2 based optical modulator



Experiment Layout

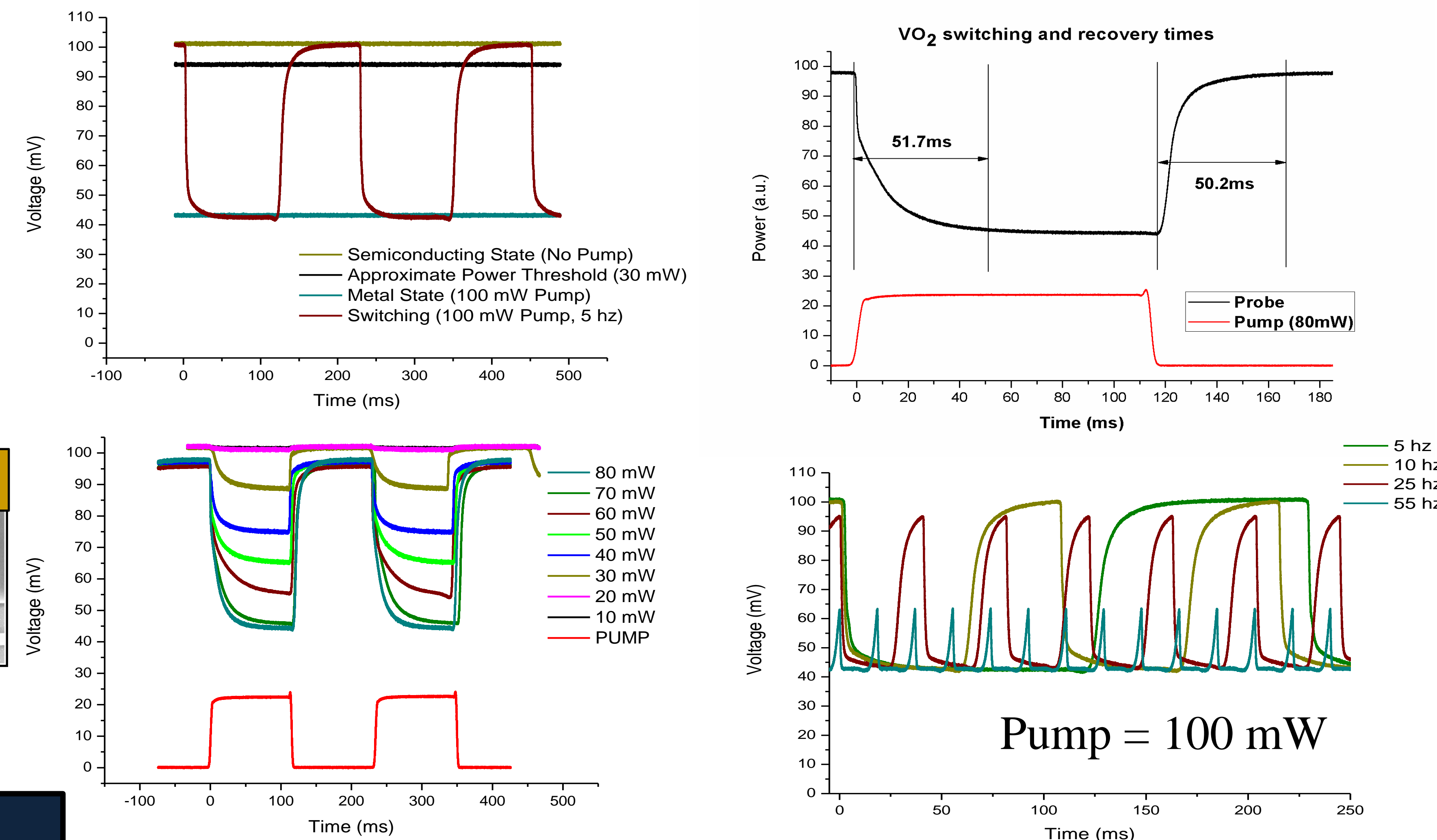


- 532 nm pump beam heats the VO_2
- 1550 nm probe beam measures transmission
- A sharp decrease in transmission occurs when the VO_2 switches.

Experimental Measurements

- 1) Minimum incident power needed to switch
- 2) Variation of transmission with incident power
- 3) Variation of signal with chopping frequency
- 4) Approximate time to reach max contrast
- 5) Approximate recovery time

Experimental Results



- Minimum power needed to switch a 150nm-film = 30 mW at 532 nm
- Maximum contrast = 60% decrease in transmission
- Saturation power = 70 mW and above
- Estimated time to max contrast = 51.7 ms, recovery time = 50.2 ms

Simulating Temperature Rise

Temperature Change with Time Heat Source: Power/Volume

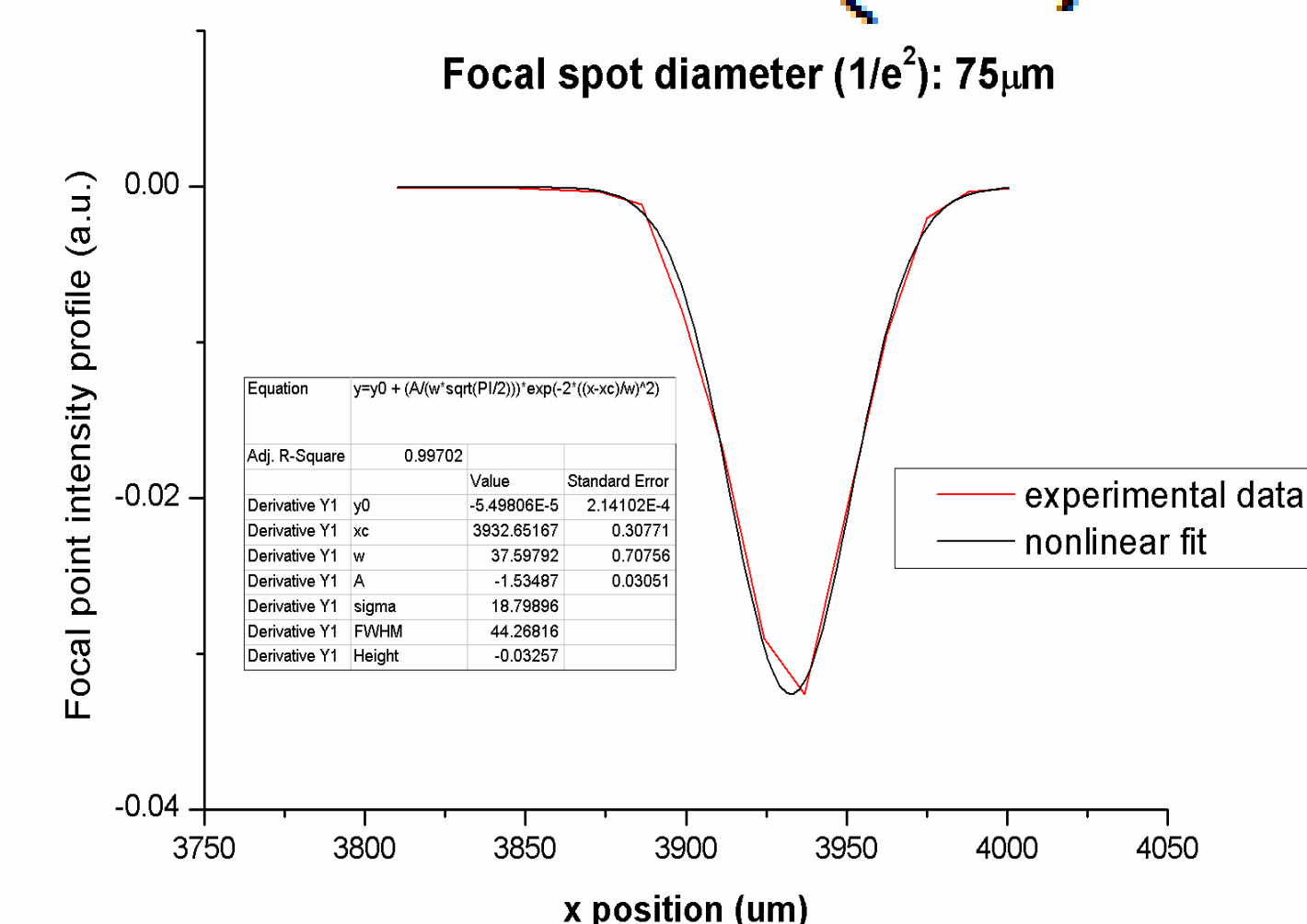
$$C_p \rho \frac{\partial T}{\partial t} - \kappa \nabla^2 T = Q$$

Heat Source Definition (3) Heat Flow Through Given Volume

$$Q = (1 - R) \gamma I_0 e^{-2(r/Rf)^2} e^{-\gamma|z|} \text{ (W/m}^3\text{)}$$

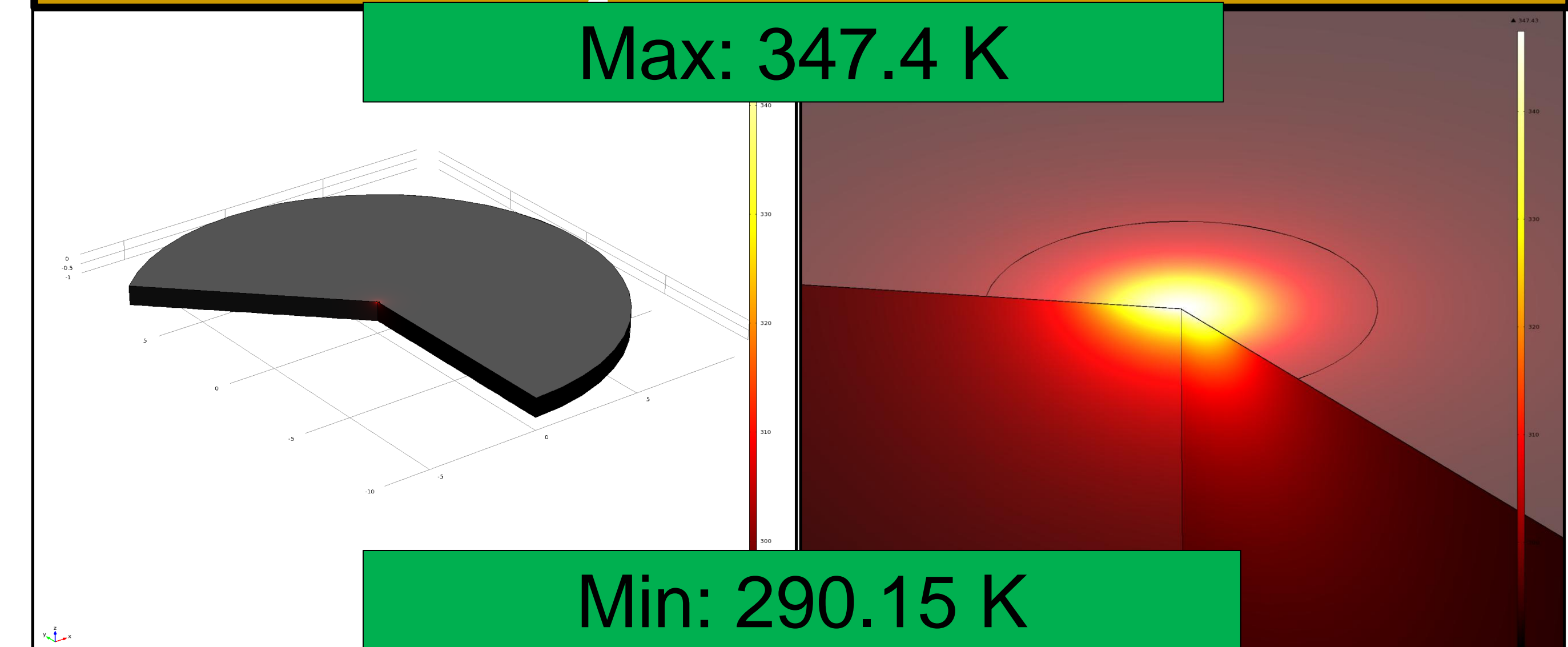
Measured Beam Parameters for 532 nm Pump

R = reflection coefficient = 0.2
 d_{ab} = absorption depth = 146 nm
 γ = absorption coefficient = $1/d_{ab}$
 Rf = focal spot radius ($1/e^2$) = 37.5 μm
 Sample Parameters
 Th = VO_2 thickness = 150 nm
 k = VO_2 thermal conductivity = 6.5 W/m K (2)
 C_p = VO_2 specific heat capacity = 656 J/kg K (2)
 ρ = VO_2 density = 4650 kg/m³ (2)
 Substrate Dimensions: 10 mm × 10 mm × 1 mm



Simulation Results

- For a pump power of 30 mW, Comsol simulations show a maximum temperature of 347.4 K for a 150 nm thick film after 1 second.
- The thin film's thickness and the wavelength dependent absorption coefficient (γ) are the major determinants of the maximum temperature.
- Since the glass substrate does not absorb any radiation, all of the heat is due to absorption within the thin film of VO_2 .



Conclusions

- 1) We successfully switched VO_2 thin films with a 532 nm laser.
- 2) For a 150 nm-film, a minimum power of 30 mW, corresponding to a minimum intensity of 679 W/cm², was needed to switch.
- 3) For a power of 30 mW, we calculated a maximum temperature rise of 347.4 K, which should be high enough for the phase transition.
- 4) The thickness of the VO_2 film and the wavelength dependent absorption coefficient determine the maximum temperature that can be attained for a given power.

The next phase for this research will be to study VO_2 's optically induced phase transition, which will involve moving to high-power, pulsed lasers. The long term goal is to design and produce a laser controlled optical modulator using VO_2 .

References/Acknowledgements

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 - (3) Grigoropoulos, Costas. "Lasers, Optics, and Thermal Considerations in Ablation Experiments." *Laser Ablation and Desorption*. Ed. John C. Miller and Richard F. Haglund, Jr Academic Press, 1998. Print.
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